AOT8N50/AOTF8N50

500V, 8A N-Channel MOSFET

General Description

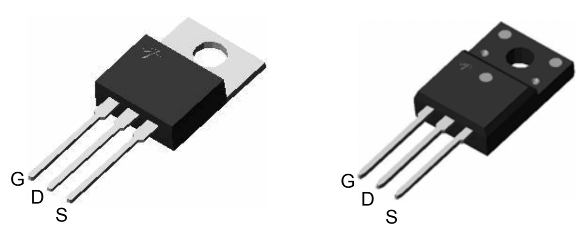
The AOT8N50 & AOTF8N50 have been fabricated using an advanced high voltage MOSFET process that is designed to deliver high levels of performance and robustness in popular AC-DC applications.
By providing low $R_{DS(on)}$, C_{iss} and C_{rss} along with guaranteed avalanche capability these parts can be adopted quickly into new and existing offline power supply designs.

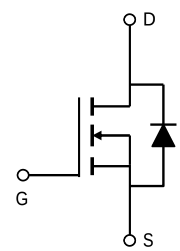
Features

V_{DS} (V) = 600V @ 150°C
I_D = 8A
$R_{DS(ON)}$ < 0.85Ω (V$_{GS}$ = 10V)

100% UIS Tested!
100% R_g Tested!

TO-220 Top View TO-220F





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	AOT8N50	AOTF8N50	Units
Drain-Source Voltage		V_{DS}	500		V
Gate-Source Voltage		V_{GS}	±30		V
Continuous Drain Current	T_C=25°C	I_D	8	8*	A
	T_C=100°C		5.6	5.6*	A
Pulsed Drain Current [C]		I_{DM}	30		A
Avalanche Current [C, G]		I_{AR}	3.2		A
Repetitive avalanche energy [C, G]		E_{AR}	154		mJ
Single pulsed avalanche energy [G]		E_{AS}	307		mJ
Peak diode recovery dv/dt		dv/dt	5		V/ns
Power Dissipation [B]	T_C=25°C	P_D	176	38.5	W
	Derate above 25°C		1.4	0.3	W/ °C
Junction and Storage Temperature Range		T_J, T_{STG}	-50 to 150		°C
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds		T_L	300		°C

Thermal Characteristics

Parameter	Symbol	AOT8N50	AOTF8N50	Units
Maximum Junction-to-Ambient [A,D]	$R_{\theta JA}$	65	65	°C/W
Maximum Case-to-Sink [A]	$R_{\theta CS}$	0.5	--	°C/W
Maximum Junction-to-Case	$R_{\theta JC}$	0.71	3.25	°C/W

* Drain current limited by maximum junction temperature.

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V, T_J=25°C	500			V
		I_D=250µA, V_{GS}=0V, T_J=150°C		600		V
BV_{DSS} /ΔT_J	Breakdown Voltage Temperature Coefficient	I_D=250µA, V_{GS}=0V		0.56		V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=500V, V_{GS}=0V			1	µA
		V_{DS}=400V, T_J=125°C			10	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±30V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250µA	3.4	4	4.6	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=4A		0.63	0.85	Ω
g_{FS}	Forward Transconductance	V_{DS}=40V, I_D=4A		10		S
V_{SD}	Diode Forward Voltage	I_S=1A, V_{GS}=0V		0.73	1	V
I_S	Maximum Body-Diode Continuous Current				8	A
I_{SM}	Maximum Body-Diode Pulsed Current				30	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=25V, f=1MHz	694	868	1042	pF
C_{oss}	Output Capacitance		74	93	112	pF
C_{rss}	Reverse Transfer Capacitance		6.2	7.8	9.4	pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz	2	4	6.0	Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=10V, V_{DS}=400V, I_D=8A		23.6	28.3	nC
Q_{gs}	Gate Source Charge			5.2	6.2	nC
Q_{gd}	Gate Drain Charge			10.6	12.7	nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=250V, I_D=8A, R_G=25Ω		19.5	323	ns
t_r	Turn-On Rise Time			47	56.4	ns
$t_{D(off)}$	Turn-Off DelayTime			51.5	62.0	ns
t_f	Turn-Off Fall Time			38.5	46.0	ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=8A,dI/dt=100A/µs,V_{DS}=100V		206	247.0	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=8A,dI/dt=100A/µs,V_{DS}=100V		2.14	2.6	µC

A. The value of $R_{\theta JA}$ is measured with the device in a still air environment with T_A =25°C.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C, Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to case $R_{\theta JC}$ and case to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300 µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-case thermal impedence which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150°C. The SOA curve provides a single pulse rating.
G. L=60mH, I_{AS}=3.2A, V_{DD}=50V, R_G=25Ω, Starting T_J=25°C

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

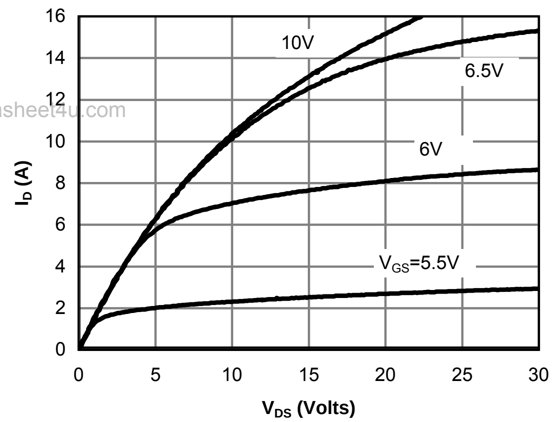


Fig 1: On-Region Characteristics

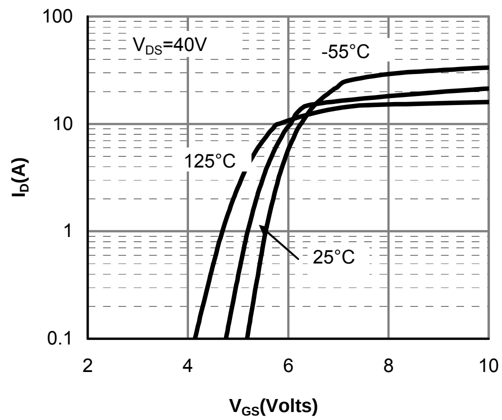


Figure 2: Transfer Characteristics

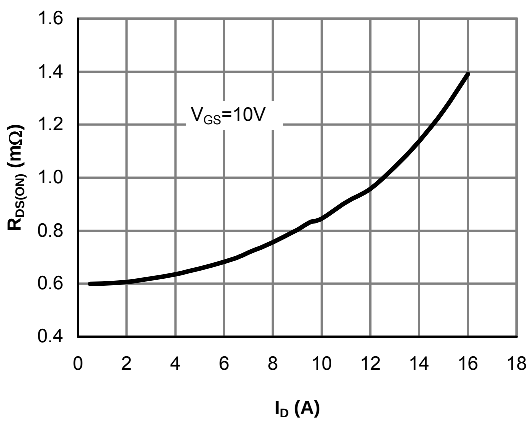


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

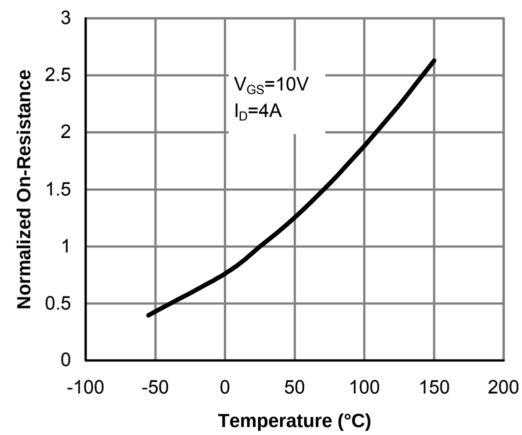


Figure 4: On-Resistance vs. Junction Temperature

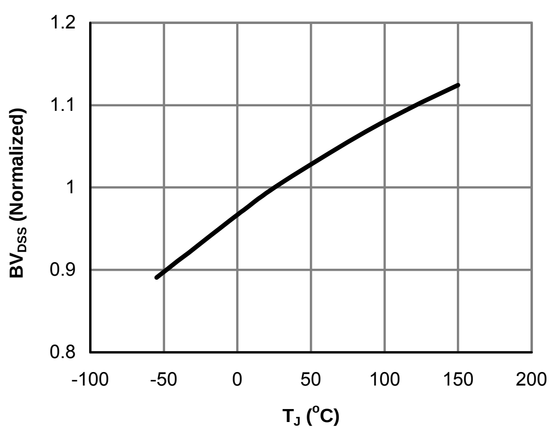


Figure 5: Break Down vs. Junction Temperature

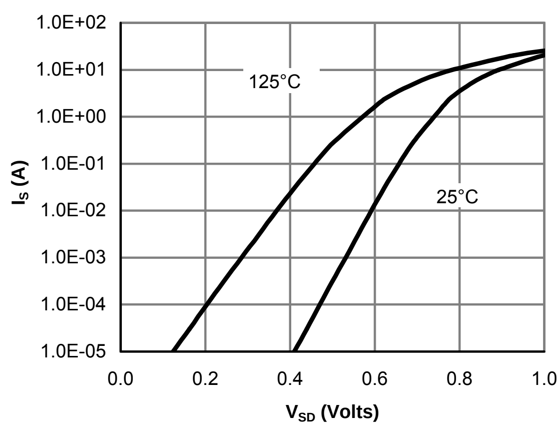


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

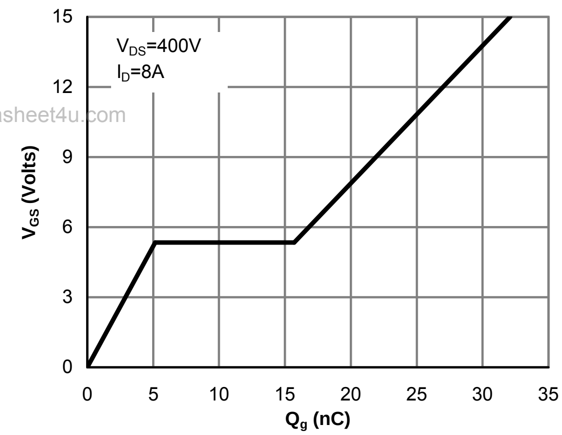


Figure 7: Gate-Charge Characteristics

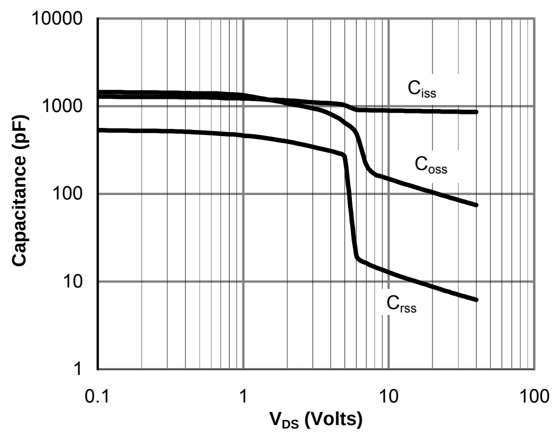


Figure 8: Capacitance Characteristics

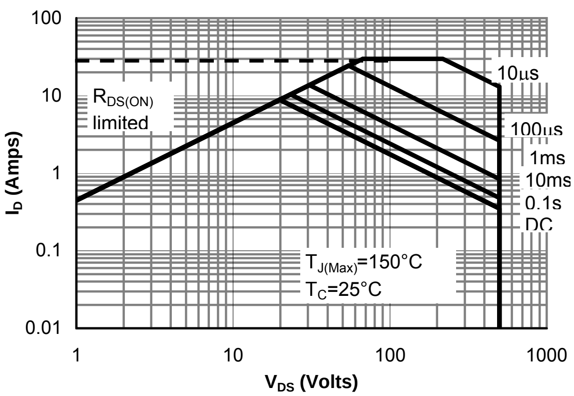


Figure 9: Maximum Forward Biased Safe Operating Area for AOT8N50 (Note F)

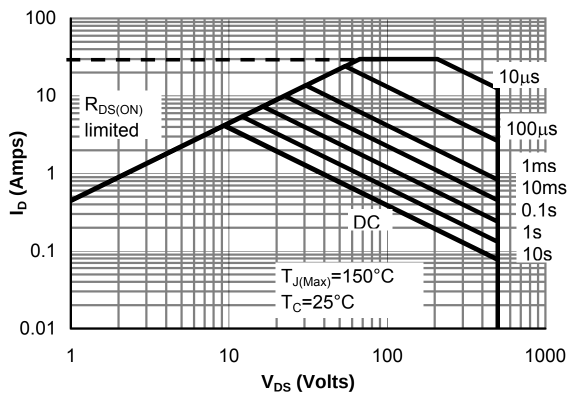


Figure 10: Maximum Forward Biased Safe Operating Area for AOTF8N50 (Note F)

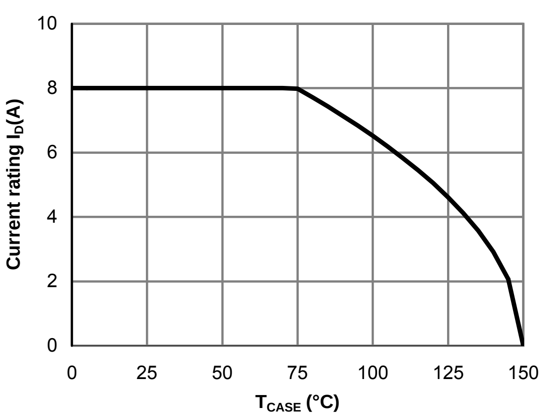


Figure 11: Current De-rating (Note B)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

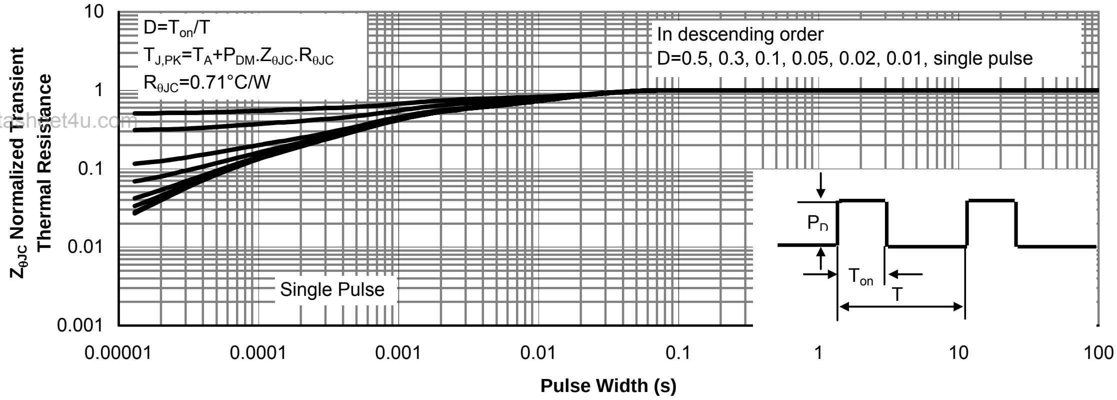


Figure 12: Normalized Maximum Transient Thermal Impedance for AOT8N50 (Note F)

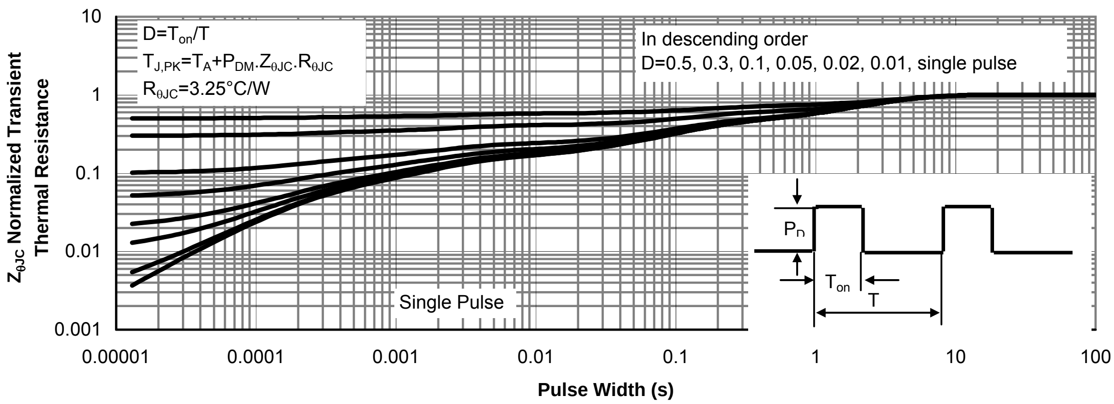
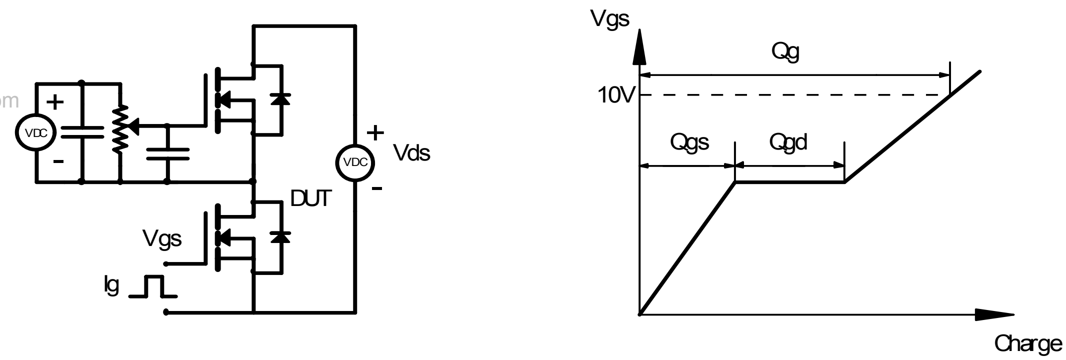
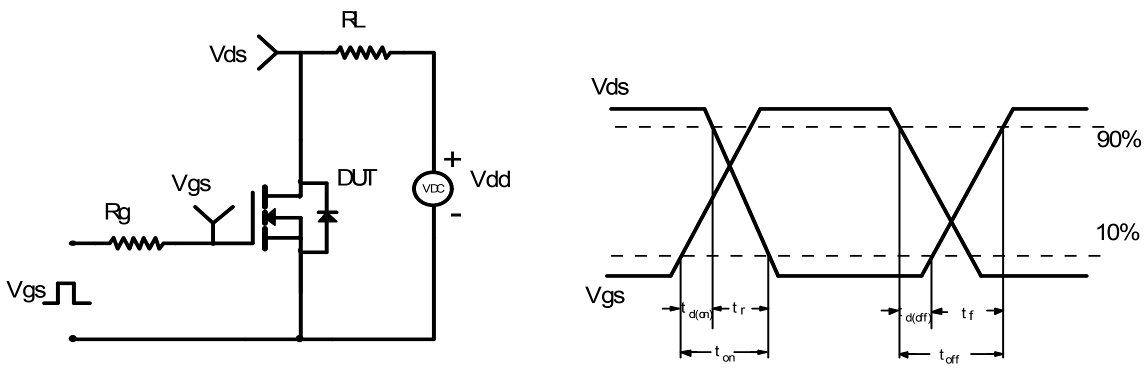


Figure 13: Normalized Maximum Transient Thermal Impedance for AOTF8N50 (Note F)

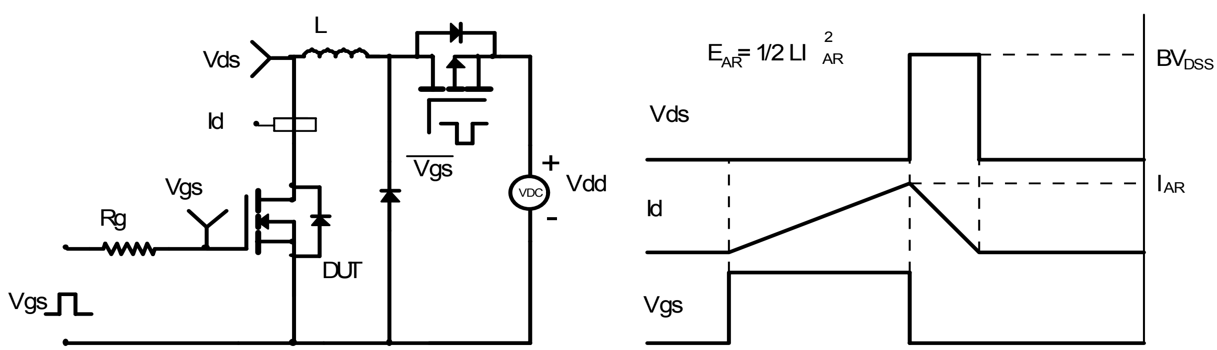
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms